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Fairchild Semiconductor PN2369

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MICO	NDUCTOR®					
		PN2369				
his device urrents of	itching Transistor e is designed for high speed saturated sw 10mA to 100mA. om process 21.	1	mitter 2. Ba	TO-92	bliector	
osolut	e Maximum Ratings* T _a =25°	² C unless otherwise noted				
Symbol	l Paramo	meter F			Units	
CEO	Collector-Emitter Voltage		15		V	
СВО	Collector-Base Voltage		40		V	
BO	Emitter-Base Voltage		4.5		V	
		inuous	200		mA	
, T _{STG}	Operating and Storage Junction T limiting values above which the serviceability of any se		-55 ~ 150		°C	
	re based on a maximum junction temperature of 150 o ady limits. The factory should be consulted on applicat					
hese are stea		ions involving pulsed or low duty cycle operations	Min.	Max.	Units	
hese are stea	ady limits. The factory should be consulted on applicat al Characteristics T _a =25°C uni Parameter	ions involving pulsed or low duty cycle operations less otherwise noted		Max.	Units	
hese are stea ectrica ymbol	ady limits. The factory should be consulted on applicat al Characteristics T _a =25°C uni Parameter	ions involving pulsed or low duty cycle operations less otherwise noted Test Condition $I_{C} = 10$ mA, $I_{B} = 0$		Max.	Units V	
hese are stea ectrica ymbol	ady limits. The factory should be consulted on applicat al Characteristics T _a =25°C uni Parameter teristics	ions involving pulsed or low duty cycle operations less otherwise noted Test Condition	Min.	Max.		
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hese are stea ectrica ymbol if Charact BR)CEO BR)CES	ady limits. The factory should be consulted on applicat Al Characteristics T _a =25°C unl Parameter teristics Collector-Emitter Breakdown Voltage * Collector-Base Breakdown Voltage Emitter-Base Breakdown Voltage	$\label{eq:loss} \begin{tabular}{ c c c c c } \hline less otherwise noted \\ \hline \hline Test Condition \\ \hline \hline I_C = 10mA, I_B = 0 \\ \hline I_C = 10\muA, V_{BE} = 0 \\ \hline I_C = 10\muA, I_E = 0 \\ \hline I_E = 10\muA, I_C = 0 \\ \hline \end{array}$	Min. 15 40		V V V V	
hese are stea ectrica ymbol if Charact BR)CEO BR)CES BR)CBO	ady limits. The factory should be consulted on applicat AI Characteristics T _a =25°C uni Parameter teristics Collector-Emitter Breakdown Voltage * Collector-Emitter Breakdown Voltage Collector-Base Breakdown Voltage	ions involving pulsed or low duty cycle operations less otherwise noted $\hline I_{C} = 10 \text{mA}, I_{B} = 0$ $I_{C} = 10 \mu\text{A}, V_{BE} = 0$ $I_{C} = 10 \mu\text{A}, I_{E} = 0$	Min. 15 40 40	Max.	V V V	
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ectrica ymbol f Charact BR)CEO BR)CES BR)CBO BR)CBO BR)EBO BO D CE E E E E(sat) BE(sat) mall Sign bo	ady limits. The factory should be consulted on applicat Parameter teristics Collector-Emitter Breakdown Voltage * Collector-Emitter Breakdown Voltage Collector-Base Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cutoff Current teristics DC Current Gain * Collector-Emitter Saturation Voltage * Base-Emitter Saturation Voltage al Characteristics Output Capacitance Input Capacitance	$\label{eq:constraint} \hline $V_{CB} = 5.0V, \ I_{E} = 0, \ T_{est} \ Condition \\ \hline $V_{CB} = 5.0V, \ I_{E} = 0, \ T_{a} = 1.0MHz \\ \hline $V_{CB} = 5.0V, \ I_{E} = 0, \ T_{a} = 1.0MHz \\ \hline $V_{CB} = 5.0V, \ I_{E} = 0, \ T_{a} = 1.0MHz \\ \hline $V_{CB} = 5.0V, \ I_{E} = 0, \ T_{a} = 1.0MHz \\ \hline $V_{CB} = 5.0V, \ I_{E} = 0, \ T_{a} = 1.0MHz \\ \hline $V_{CB} = 5.0V, \ I_{C} = 0, \ T_{a} = 1.0MHz \\ \hline $V_{CB} = 5.0V, \ T_{C} = 0, \ T_{a} = 1.0MHz \\ \hline $V_{CB} = 0.5V, \ T_{C} = 0, \ T_{a} = 1.0MHz \\ \hline $V_{CB} = 0.5V, \ T_{C} = 0, \ T_{a} = 1.0MHz \\ \hline $V_{CB} = 0.5V, \ T_{C} = 0, \ T_{a} = 1.0MHz \\ \hline $V_{CB} = 0.5V, \ T_{C} = 0, \ T_{a} = 1.0MHz \\ \hline $V_{CB} = 0.5V, \ T_{C} = 0, \ T_{a} = 1.0MHz \\ \hline $V_{CB} = 0.5V, \ T_{C} = 0, \ T_{a} = 1.0MHz \\ \hline $V_{CB} = 0.5V, \ T_{C} = 0, \ T_{a} = 0.0MHz \\ \hline $V_{CB} = 0.5V, \ T_{C} = 0, \ T_{a} = 0.0MHz \\ \hline $V_{CB} = 0.5V, \ T_{C} = 0, \ T_{a} = 0.0MHz \\ \hline $V_{CB} = 0.5V, \ T_{C} = 0, \ T_{a} = 0.0MHz \\ \hline $V_{CB} = 0.5V, \ T_{C} = 0, \ T_{a} = 0.0MHz \\ \hline $V_{CB} = 0.5V, \ T_{C} = 0, \ T_{a} = 0.0MHz \\ \hline $V_{CB} = 0.5V, \ T_{C} = 0, \ T_{a} = 0.0MHz \\ \hline $V_{CB} = 0.5V, \ T_{C} = 0, \ T_{a} = 0.0MHz \\ \hline $V_{CB} = 0.5V, \ T_{C} = 0, \ T_{a} = 0.0MHz \\ \hline $V_{CB} = 0.5V, \ T_{C} = 0, \ T_{a} = 0.0MHz \\ \hline $V_{CB} = 0.5V, \ T_{a} = 0.0V, \ T_{a} = 0.0MHz \\ \hline $V_{CB} = 0.5V, \ T_{a} = 0.0MHz \\ \hline $V_{CB} = 0.5V, \ T_{a} = 0.0MHz \\ \hline $V_{CB} = 0.0MHz$	Min. 15 40 40 4.5 40 20 0.7	0.4 30 120 0.25 0.85 4.0	V V V V μA μA V V PF	
hese are stea eCtriCa ymbol ff Charact BR)CEO BR)CES BR)CBO BR)CBO BR)EBO BO n Charact E CE(sat) BE(sat) mall Signa bo	ady limits. The factory should be consulted on applicat Parameter teristics Collector-Emitter Breakdown Voltage * Collector-Emitter Breakdown Voltage Collector-Base Breakdown Voltage Collector-Base Breakdown Voltage Collector Cutoff Current teristics DC Current Gain * Collector-Emitter Saturation Voltage * Base-Emitter Saturation Voltage * Base-Emitter Saturation Voltage al Characteristics Output Capacitance Input Capacitance Small -Signal Current Gain	$\label{eq:constraint} \hline $V_{CB} = 0.5V, \ I_C = 10mA, \ I_B = 0$ \\ \hline $I_C = 10\muA, \ V_{BE} = 0$ \\ \hline $I_C = 10\muA, \ V_{BE} = 0$ \\ \hline $I_C = 10\muA, \ I_E = 0$ \\ \hline $I_C = 10\muA, \ I_E = 0$ \\ \hline $V_{CB} = 20V, \ I_E = 0$ \\ \hline $V_{CB} = 20V, \ I_E = 0$ \\ \hline $V_{CB} = 20V, \ I_E = 0$ \\ \hline $V_{CB} = 20V, \ I_E = 0$ \\ \hline $V_{CB} = 20V, \ I_E = 0$ \\ \hline $V_{CB} = 20V, \ I_E = 0$ \\ \hline $V_{CB} = 20V, \ I_E = 0$ \\ \hline $V_{CB} = 20V, \ I_E = 0$ \\ \hline $V_{CB} = 20V, \ I_E = 0$ \\ \hline $V_{CB} = 2.0V$ \\ \hline $I_C = 10mA, \ V_{CE} = 2.0V$ \\ \hline $I_C = 10mA, \ I_B = 1.0mA$ \\ \hline $V_{CB} = 5.0V, \ I_E = 0$ \\ \hline $F_{CB} = 0.5V, \ I_C = 0$ \\ \hline $f = 1.0MHz$ \\ \hline $V_{CB} = 2.0k\Omega$ \\ \hline $I_C = 10mA, \ V_{CE} = 10V, \ R_G = 2.0k\Omega$ \\ \hline $f = 100MHz$ \\ \hline $I_{B1} = I_{B2} = I_C = 10mA$ \\ \hline $V_{CB} = 100mA$ \\ \hline$	Min. 15 40 40 4.5 40 20 0.7 5.0	0.4 30 120 0.25 0.85 4.0 5.0	V V V V μA μA V V PF	
hese are stea eCtriCa ymbol ff Charact BR)CEO BR)CES BR)CBO BR)CBO BR)EBO BO n Charact E CE(sat) BE(sat) mall Signa bo	ady limits. The factory should be consulted on applicat Parameter teristics Collector-Emitter Breakdown Voltage * Collector-Emitter Breakdown Voltage Collector-Base Breakdown Voltage Collector-Base Breakdown Voltage Collector Cutoff Current teristics DC Current Gain * Collector-Emitter Saturation Voltage * Base-Emitter Saturation Voltage * Base-Emitter Saturation Voltage al Characteristics Output Capacitance Input Capacitance Small -Signal Current Gain	$\label{eq:constraint} \hline $V_{CB} = 5.0V, \ I_{C} = 10 \ MA, \ I_{B} = 0 $$ V_{CB} = 2.0V, \ I_{E} = 0 $$ V_{CB} = 2.0V, \ I_{E} = 0, \ T_{a} = 125^{\circ}C $$ V_{CB} = 20V, \ I_{E} = 0, \ T_{a} = 125^{\circ}C $$ V_{CB} = 2.0V, \ I_{E} = 0, \ T_{B} = 1.0MA $$ V_{CE} = 2.0V $$ I_{C} = 100 \ MA, \ V_{CE} = 2.0V $$ I_{C} = 100 \ MA, \ I_{B} = 1.0MA $$ I_{C} = 10 \ MA, \ I_{B} = 1.0MA $$ I_{C} = 10 \ MA, \ I_{B} = 1.0MA $$ I_{C} = 10 \ MA, \ I_{C} = 0, \ f = 1.0MHz $$ V_{CB} = 2.0V, \ I_{C} = 0, \ f = 1.0MHz $$ V_{CB} = 2.0V, \ I_{C} = 100 \ MA, \ V_{CE} = 10V, \ R_{G} = 2.0K\Omega $$ f = 100 \ MHz $$ V_{CB} = 0.0V, \ R_{C} = 0, \ F = 100 \ MHz $$ V_{CB} = 0.0V, \ R_{C} = 0, \ F = 100 \ MHz $$ V_{CB} = 0.0V, \ R_{C} = 0.0V, \$	Min. 15 40 40 4.5 40 20 0.7 5.0	0.4 30 120 0.25 0.85 4.0 5.0	V V V V μA μA V V PF pF	

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* Pulse Test: Pulse Width $\leq 300 \mu s, \, \text{Duty Cycle} \leq 2.0\%$

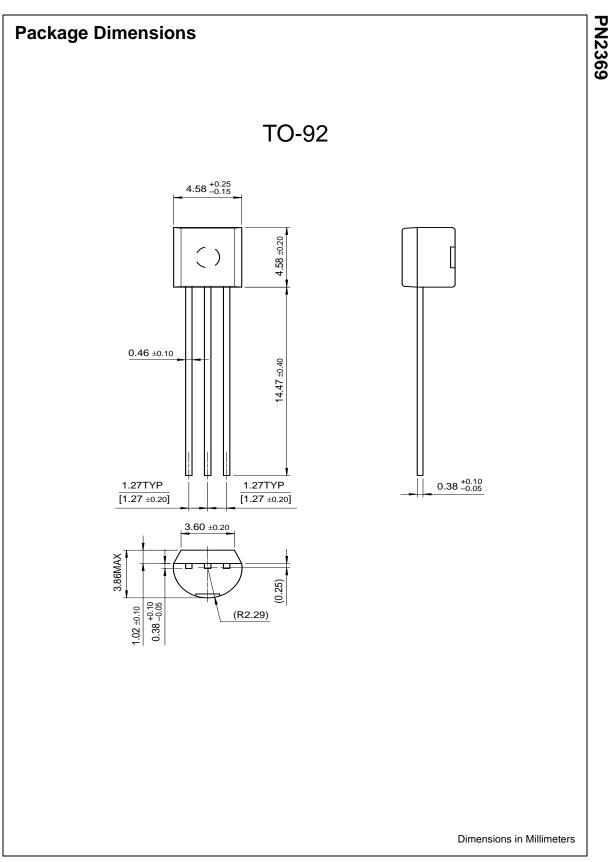
Rev. A, January 2004



Symbol	Parameter	Max.	Units
D	Total Device Dissipation Derate above 25°C	350 2.8	mW mW/°C
R ^{ejC}	Thermal Resistance, Junction to Case	125	°C/W
030 R _{θJA}	Thermal Resistance, Junction to Ambient	357	°C/W

PN2369





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CROSSVOLT™	GlobalOptoisolator™	MICROWIRE™	QT Optoelectronics [™]	TinyLogic [®]
DOME™	GTO™	MSX™	Quiet Series™	TINYOPTO™
EcoSPARK™	HiSeC™	MSXPro™	RapidConfigure™	TruTranslation™
E ² CMOS™	I ² C [™]	OCX™	RapidConnect™	UHC™
EnSigna™	ImpliedDisconnect™	OCXPro™	SILENT SWITCHER®	UltraFET [®]
FACT™	ISOPLANAR™	OPTOLOGIC [®]	SMART START™	VCX™
Across the board.	Around the world. [™]	OPTOPLANAR™	SPM™	
The Power Franc	hise™	PACMAN™	Stealth™	
Programmable Ac	tive Droop™	POP™	SuperFET™	

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.